

# Thyristors

# BT152X series

## GENERAL DESCRIPTION

Glass passivated thyristors in a full pack, plastic envelope, intended for use in applications requiring high bidirectional blocking voltage capability and high thermal cycling performance. Typical applications include motor control, industrial and domestic lighting, heating and static switching.

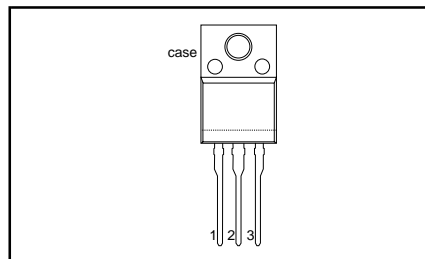
## QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	MAX.	MAX.	UNIT
$V_{DRM}$ , $V_{RRM}$	Repetitive peak off-state voltages	<b>400R</b> 450	<b>600R</b> 650	<b>800R</b> 800	V
$I_{T(AV)}$	Average on-state current	13	13	13	A
$I_{T(RMS)}$	RMS on-state current	20	20	20	A
$I_{TSM}$	Non-repetitive peak on-state current	200	200	200	A

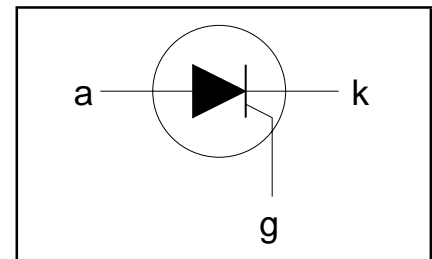
## PINNING - SOT186A

PIN	DESCRIPTION
1	cathode
2	anode
3	gate
case	isolated

## PIN CONFIGURATION



## SYMBOL



## LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.			UNIT
$V_{DRM}$	Repetitive peak off-state voltages		-	<b>-400R</b> 450 <sup>1</sup>	<b>-600R</b> 650 <sup>1</sup>	<b>-800R</b> 800	V
$I_{T(AV)}$	Average on-state current	half sine wave; $T_{hs} \leq 43^\circ\text{C}$	-	13			A
$I_{T(RMS)}$	RMS on-state current	all conduction angles	-	20			A
$I_{TSM}$	Non-repetitive peak on-state current	half sine wave; $T_j = 25^\circ\text{C}$ prior to surge $t = 10\text{ ms}$	-	200			A
		$t = 8.3\text{ ms}$	-	220			A
$I^2t$	$I^2t$ for fusing	$t = 10\text{ ms}$	-	200			A <sup>2</sup> s
$di_T/dt$	Repetitive rate of rise of on-state current after triggering	$I_{TM} = 50\text{ A}$ ; $I_G = 0.2\text{ A}$ ; $di_G/dt = 0.2\text{ A}/\mu\text{s}$	-	200			A/ $\mu\text{s}$
$I_{GM}$	Peak gate current		-	5			A
$V_{GM}$	Peak gate voltage		-	5			V
$V_{RGM}$	Peak reverse gate voltage		-	5			V
$P_{GM}$	Peak gate power		-	20			W
$P_{G(AV)}$	Average gate power	over any 20 ms period	-	0.5			W
$T_{stg}$	Storage temperature		-40	150			$^\circ\text{C}$
$T_j$	Operating junction temperature		-	125			$^\circ\text{C}$

<sup>1</sup> Although not recommended, off-state voltages up to 800V may be applied without damage, but the thyristor may switch to the on-state. The rate of rise of current should not exceed 15 A/ $\mu\text{s}$ .

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**ISOLATION LIMITING VALUE & CHARACTERISTIC** $T_{hs} = 25\text{ °C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{isol}$	R.M.S. isolation voltage from all three terminals to external heatsink	$f = 50\text{-}60\text{ Hz}$ ; sinusoidal waveform; $R.H. \leq 65\%$ ; clean and dustfree	-		2500	V
$C_{isol}$	Capacitance from T2 to external heatsink	$f = 1\text{ MHz}$	-	10	-	pF

**THERMAL RESISTANCES**

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$R_{th\ j\text{-}hs}$	Thermal resistance junction to heatsink	with heatsink compound	-	-	4.0	K/W
$R_{th\ j\text{-}hs}$	Thermal resistance junction to heatsink	without heatsink compound	-	-	5.5	K/W
$R_{th\ j\text{-}a}$	Thermal resistance junction to ambient	in free air	-	55	-	K/W

**STATIC CHARACTERISTICS** $T_j = 25\text{ °C}$  unless otherwise stated

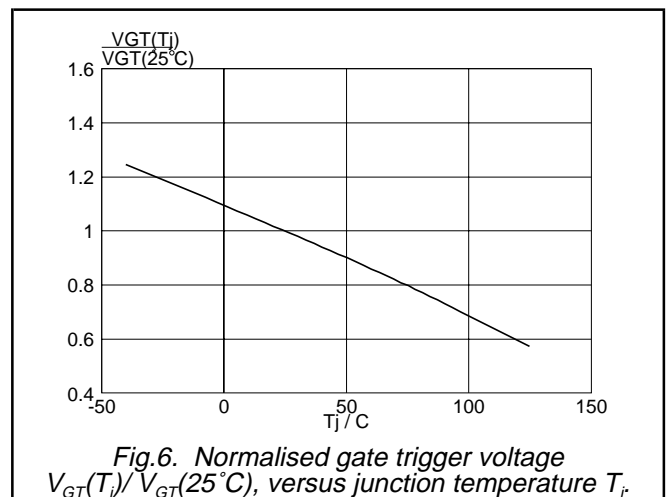
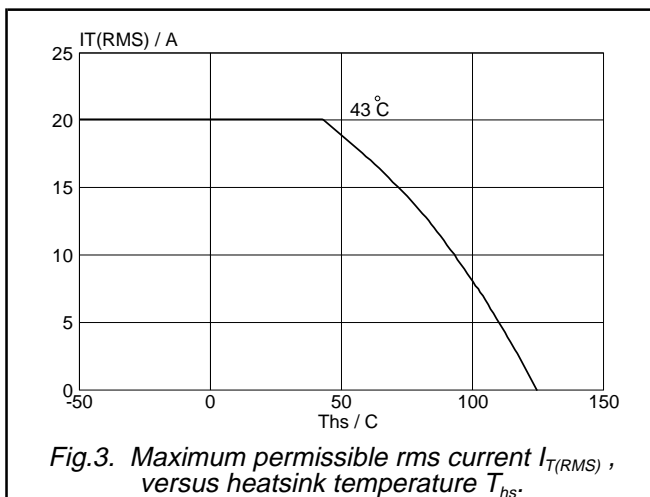
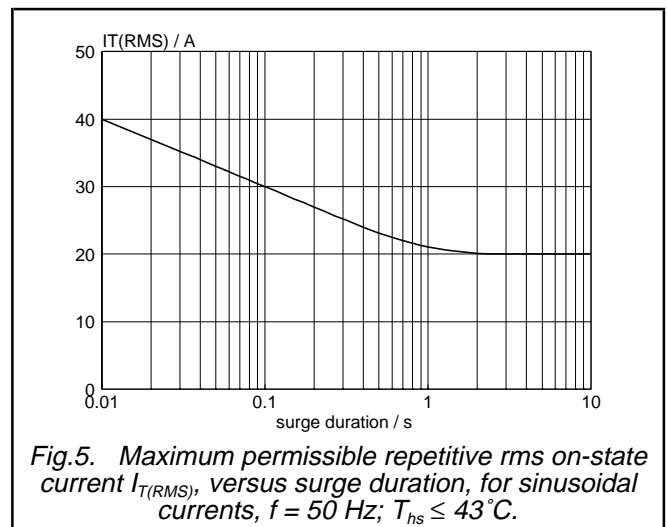
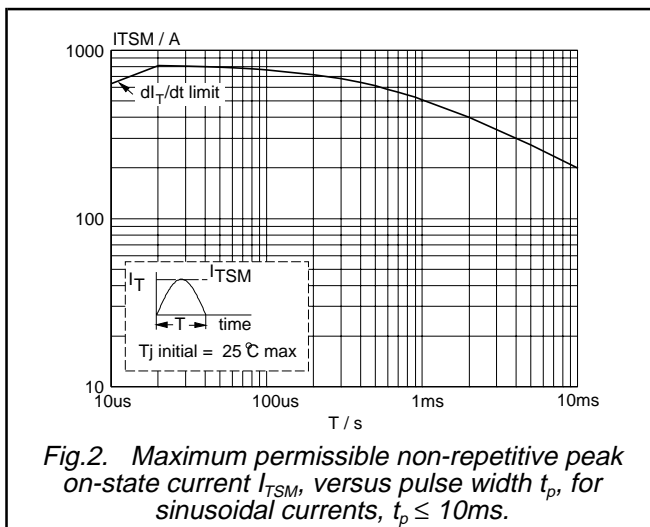
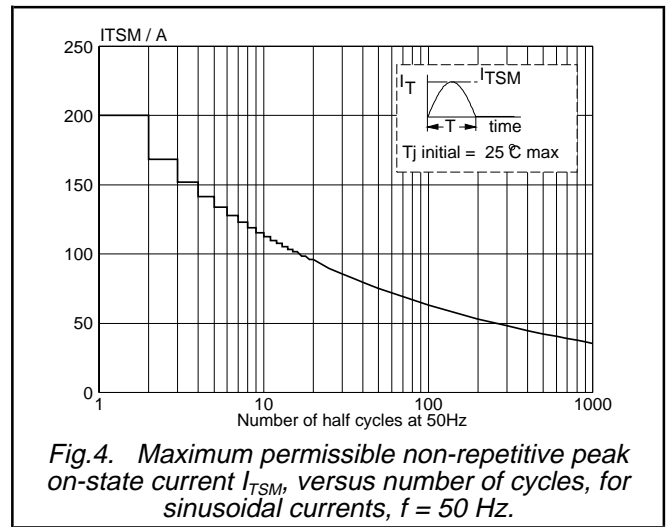
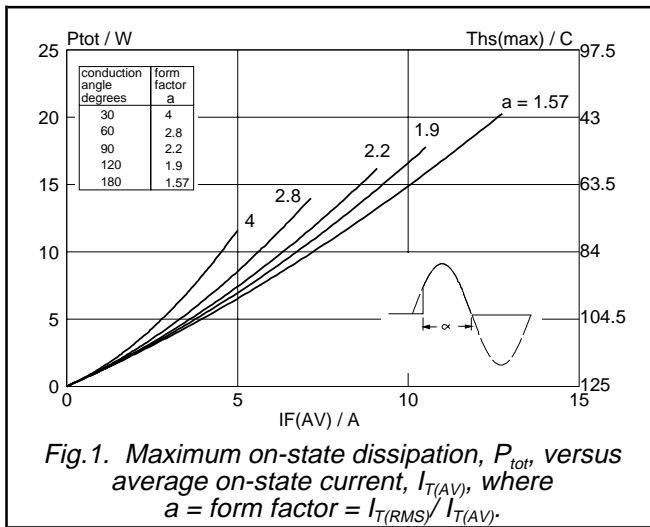
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$I_{GT}$	Gate trigger current	$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$	-	3	32	mA
$I_L$	Latching current	$V_D = 12\text{ V}$ ; $I_{GT} = 0.1\text{ A}$	-	25	80	mA
$I_H$	Holding current	$V_D = 12\text{ V}$ ; $I_{GT} = 0.1\text{ A}$	-	15	60	mA
$V_T$	On-state voltage	$I_T = 40\text{ A}$	-	1.4	1.75	V
$V_{GT}$	Gate trigger voltage	$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$	-	0.6	1.5	V
$I_D, I_R$	Off-state leakage current	$V_D = V_{DRM(max)}$ ; $I_T = 0.1\text{ A}$ ; $T_j = 125\text{ °C}$	0.25	0.4	-	V
		$V_D = V_{DRM(max)}$ ; $V_R = V_{RRM(max)}$ ; $T_j = 125\text{ °C}$	-	0.2	1.0	mA

**DYNAMIC CHARACTERISTICS** $T_j = 25\text{ °C}$  unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$dV_D/dt$	Critical rate of rise of off-state voltage	$V_{DM} = 67\% V_{DRM(max)}$ ; $T_j = 125\text{ °C}$ ; exponential waveform gate open circuit	200	300	-	V/ $\mu$ s
$t_{gt}$	Gate controlled turn-on time	$V_D = V_{DRM(max)}$ ; $I_G = 0.1\text{ A}$ ; $dI_G/dt = 5\text{ A}/\mu\text{s}$ ; $I_{TM} = 40\text{ A}$	-	2	-	$\mu$ s
$t_q$	Circuit commutated turn-off time	$V_D = 67\% V_{DRM(max)}$ ; $T_j = 125\text{ °C}$ ; $I_{TM} = 50\text{ A}$ ; $V_R = 25\text{ V}$ ; $dI_{TM}/dt = 30\text{ A}/\mu\text{s}$ ; $dV_D/dt = 50\text{ V}/\mu\text{s}$ ; $R_{GK} = 100\ \Omega$	-	70	-	$\mu$ s

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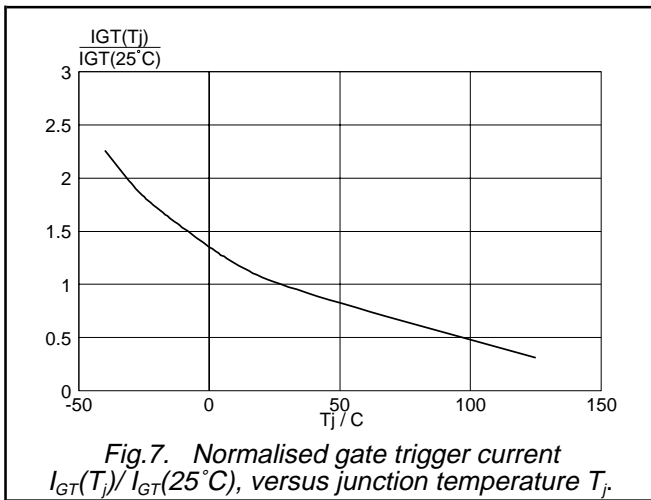


Fig. 7. Normalised gate trigger current  $I_{GT}(T_j) / I_{GT}(25^\circ\text{C})$ , versus junction temperature  $T_j$ .

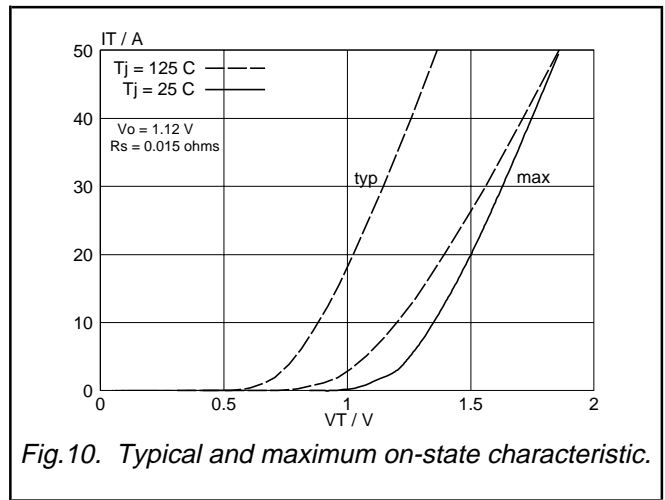


Fig. 10. Typical and maximum on-state characteristic.

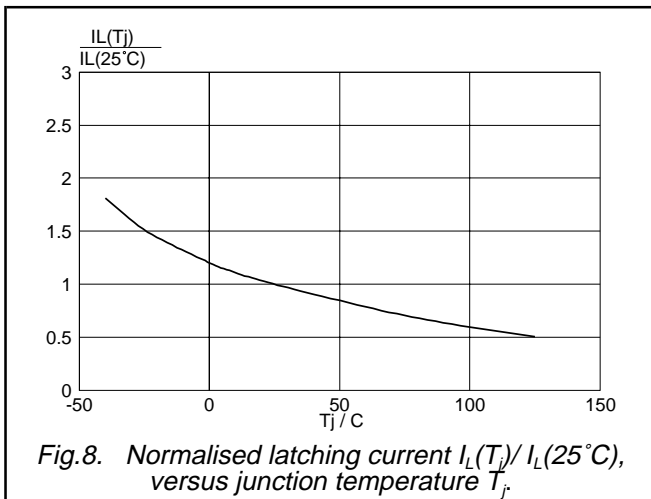


Fig. 8. Normalised latching current  $I_L(T_j) / I_L(25^\circ\text{C})$ , versus junction temperature  $T_j$ .

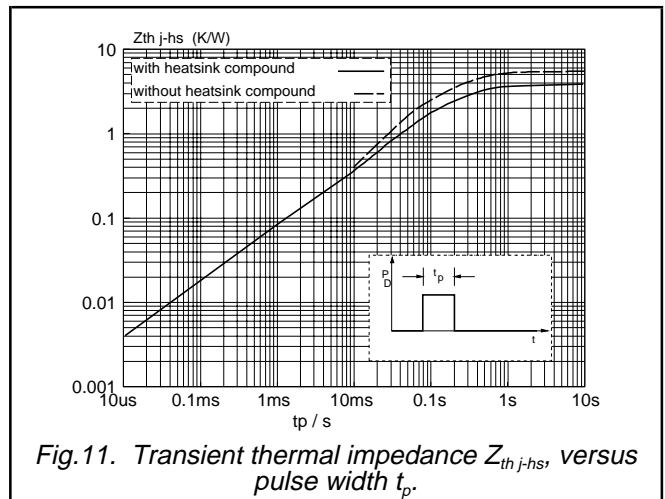


Fig. 11. Transient thermal impedance  $Z_{th \text{ j-hs}}$ , versus pulse width  $t_p$ .

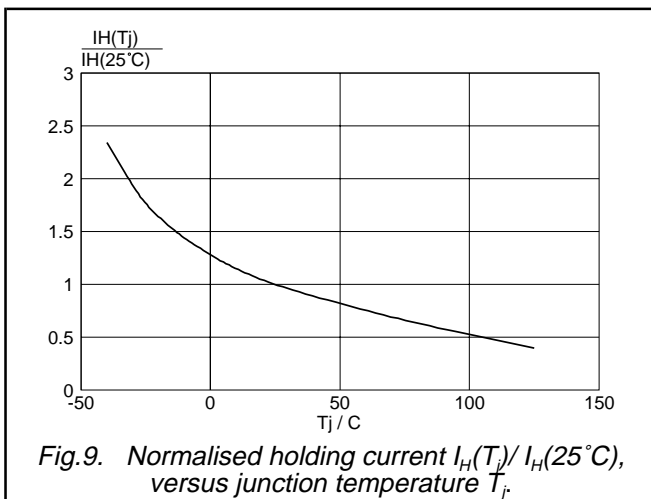


Fig. 9. Normalised holding current  $I_H(T_j) / I_H(25^\circ\text{C})$ , versus junction temperature  $T_j$ .

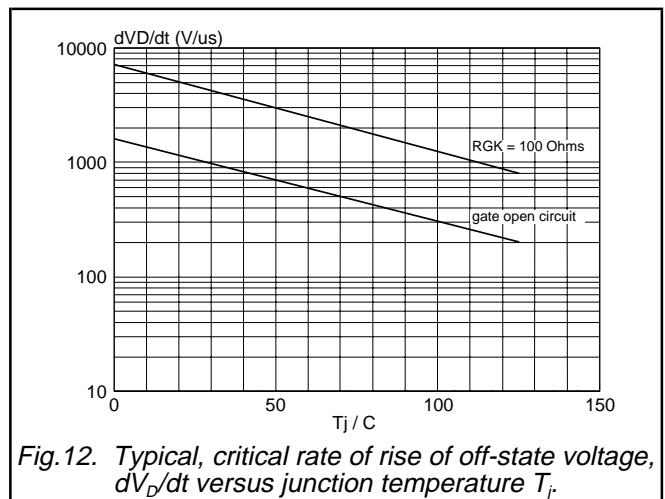


Fig. 12. Typical, critical rate of rise of off-state voltage,  $dV_D/dt$  versus junction temperature  $T_j$ .

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**MECHANICAL DATA**

*Dimensions in mm*

*Net Mass: 2 g*

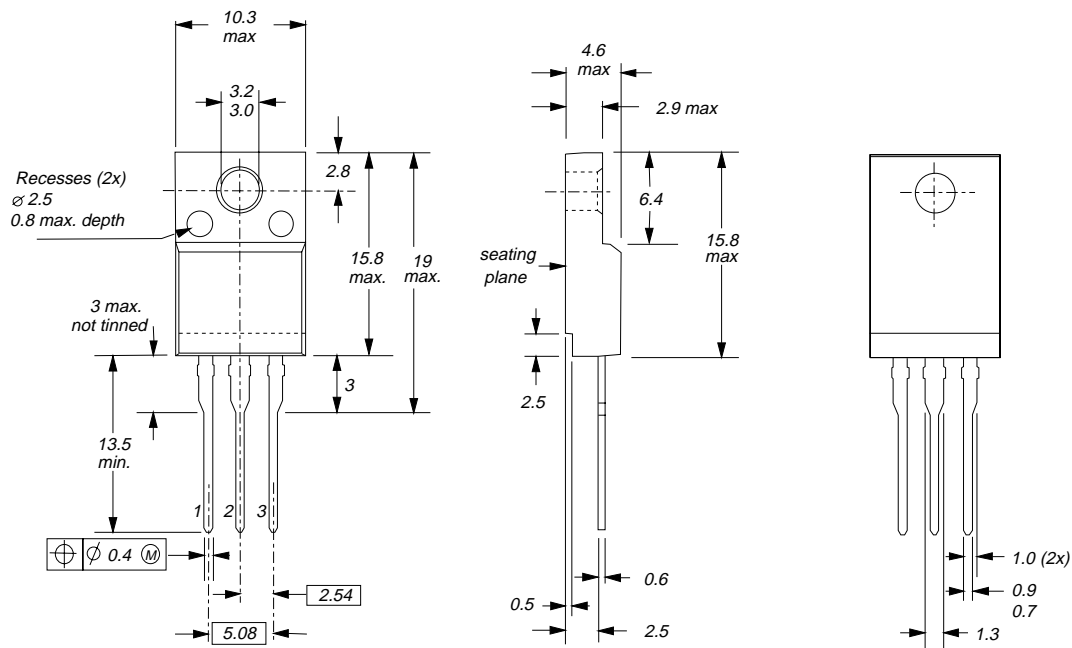


Fig. 13. SOT186A; The seating plane is electrically isolated from all terminals.

**Notes**

1. Refer to mounting instructions for F-pack envelopes.
2. Epoxy meets UL94 V0 at 1/8".

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**DEFINITIONS**

<b>Data sheet status</b>	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
<b>Limiting values</b>	
Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
<b>Application information</b>	
Where application information is given, it is advisory and does not form part of the specification.	
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